

## Features

- Trench Power LV MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(ON)</sub>
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

#### **Maximum Ratings**

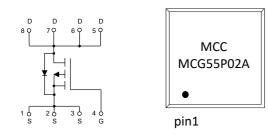
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 3.3°C/W Junction to Case<sup>(2)</sup>
- Thermal Resistance: 39°C/W Junction to Ambient<sup>(2)</sup>

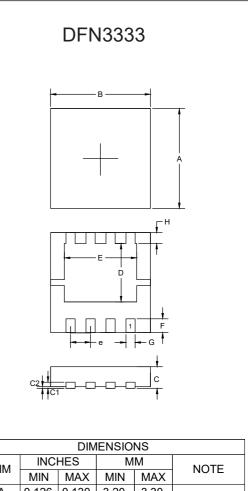
Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-20	V	
Gate-Source Volltage	V <sub>GS</sub>	±10	V	
Continuous Drain Current	I <sub>D</sub>	-55		
Pulsed Drain Current <sup>(3)</sup>		I <sub>DM</sub>	-160	A
Total Power Dissipation	T <sub>C</sub> =25°C	- P <sub>D</sub>	38	W
	T <sub>A</sub> =25°C	- FD	3.2	W
Single Pulsed Avalanche Energy		E <sub>AS</sub>	75	mJ

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2.  $R_{BJA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{BJC}$  is guaranteed by design, while  $R_{BJA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.
- 3. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.

## Internal Structure and Marking Code





**P-CHANNEL** 

MOSFET

DIM	INC	INCHES MM		NOTE	
	MIN	MAX	MIN	MAX	NOTE
Α	0.126	0.130	3.20	3.30	
В	0.126	0.130	3.20	3.30	
С	0.030	0.033	0.75	0.85	
C1	0.007	0.009	0.18	0.22	
C2		0.002		0.05	
D	0.071	0.079	1.80	2.00	
E	0.087	0.098	2.20	2.50	
F	0.016	0.020	0.40	0.50	
G	0.010	0.014	0.25	0.35	
Н	0.012	0.016	0.30	0.40	
е	0.024	0.028	0.60	0.70	

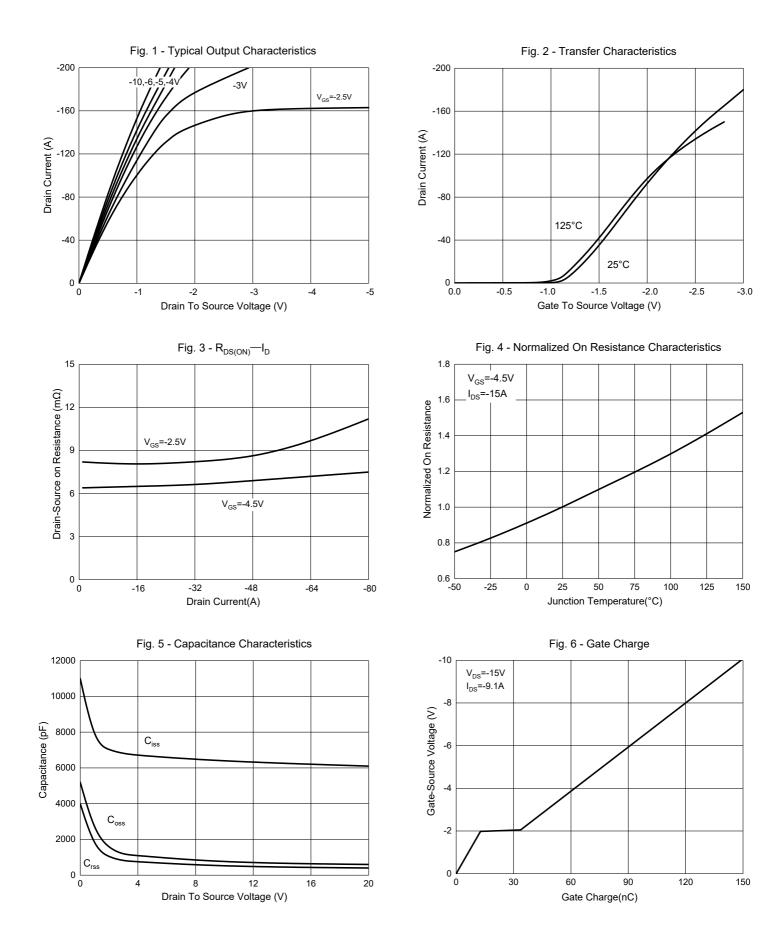


## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics					I	I	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250µA	-20			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , Ι <sub>D</sub> =-250μΑ	-0.4	-0.62	-1.0	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-15A		6.5	8.3	mΩ	
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-10A		8	10	mΩ	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-8A		10.3	15	mΩ	
Diode Characteristics			1		1	1	
Continuous Body Diode Current	Is				-55	A	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A			-1.3	V	
Reverse Recovery Time	t <sub>rr</sub>			46		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =-6A, dI <sub>F</sub> /dt=100A/μs		25.2		nC	
Dynamic Characteristics					1		
Input Capacitance	C <sub>iss</sub>			6358			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-10V,V <sub>GS</sub> =0V,f=1MHz		690		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			477			
Total Gate Charge	Qg			149			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-9.1A		12.7		nC	
Gate-Drain Charge	Q <sub>gd</sub>			21			
Turn-On Delay Time	t <sub>d(on)</sub>			11			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =-15V, V <sub>GEN</sub> =-10V,		36			
Turn-Off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> =2.5Ω, I <sub>DS</sub> =-6A		182		- ns	
Turn-Off Fall Time	t <sub>f</sub>			191			



# **Curve Characteristics**





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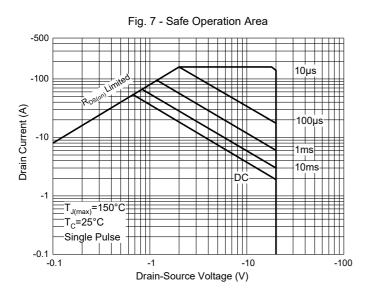
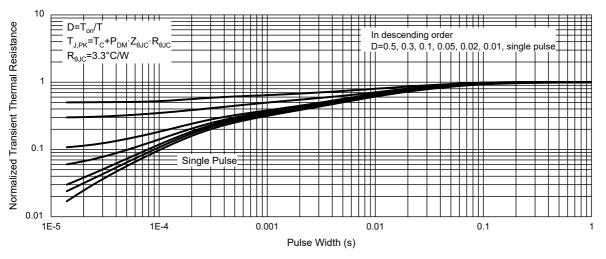


Fig. 8 - Normalized Maximum Transient Thermal Impedance





MCG55P02/

# **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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